

isc N-Channel MOSFET Transistor

IPD50R800CE,IIPD50R800CE

• FEATURES

- Static drain-source on-resistance:
 $R_{DS(on)} \leq 800m\Omega$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

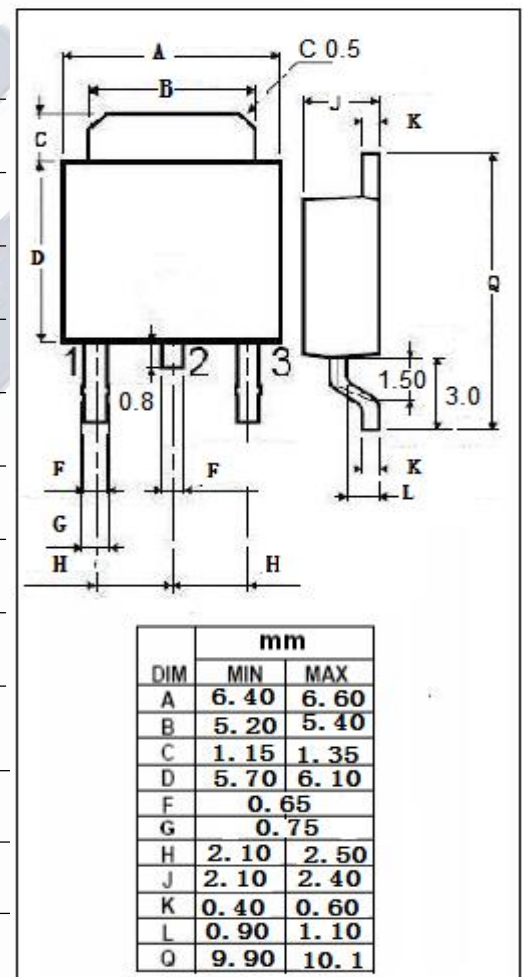
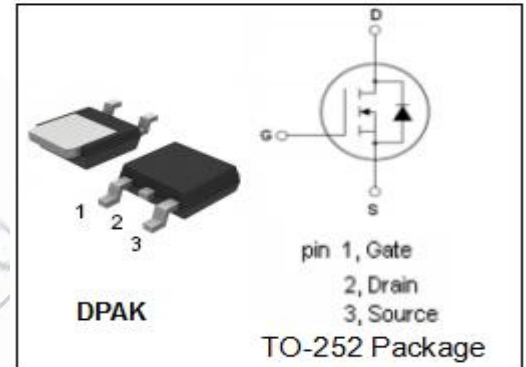
- Fast switching

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	500	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	7.6	A
I_{DM}	Drain Current-Single Pulsed	15.5	A
P_D	Total Dissipation @ $T_c=25^\circ C$	60	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Channel-to-case thermal resistance	2.07	$^\circ C/W$
$R_{th(j-a)}$	Channel-to-ambient thermal resistance	62	$^\circ C/W$



isc N-Channel MOSFET Transistor IPD50R800CE,IIPD50R800CE

ELECTRICAL CHARACTERISTICS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=1mA$	500			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.13\mu A$	2.5		3.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=13V; I_D=1.3A$			800	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=20V$			0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=500V; V_{GS}=0V$			1	μA
V_{SD}	Diode forward voltage	$I_F=1.9A, V_{GS}=0V$		0.83		V